



P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
201/	7mΩ @ V _{GS} = -10V	-90A
-30V	16mΩ @ V _G S = -4.5V	-60A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power-management functions
- DC-DC converters

Features and Benefits

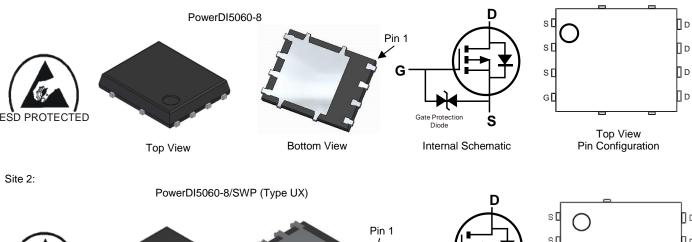
- Low RDS(ON) Minimizes On-State Losses
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- 100% Unclamped Inductive Switching, Test in Production -Ensures More Reliable and Robust End Application
- **ESD Protected Gate**
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP3007SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

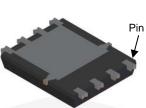
- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

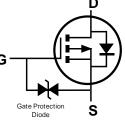
Site 1:











Пο ħο Dο Пο Top View

Top View

Bottom View

Internal Schematic

Pin Configuration

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

DMP3007SPSQ Document number: DS41832 Rev. 3 - 2

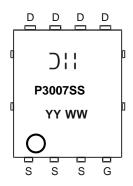


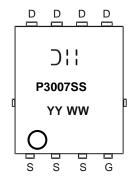
Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Number	Package	Qty.	Carrier	
DMP3007SPSQ-13	PowerDI5060-8	2,500	Tape & Reel	
DIMF30073F3Q-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel	

Note:

Marking Information





⊃¦¦ = Manufacturer's Marking P3007SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 23 = 2023) WW = Week (01 to 53)

Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-30	V
Gate-Source Voltage	Vgss	±25	V	
Continuous Drain Current Vac. 40V (Note 5)	$T_C = +25^{\circ}C$	lD	-90	- A
Continuous Drain Current, Vgs = -10V (Note 5)	$T_C = +70$ °C		-70	
Maximum Continuous Body Diode Forward Current (Note 5)	Is	-90	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-160	Α
Avalanche Current, L = 1mH (Note 6)		las	-16	Α
Avalanche Energy, L = 1mH (Note 6)		E _{AS}	130	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	T _A = +25°C	PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	Reja	90	°C/W
Total Power Dissipation (Note 8)	T _A = +25°C	P _D	2.7	W
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	Reja	47	°C/W
Total Power Dissipation (Note 5)	Tc = +25°C	PD	80	W
Thermal Resistance, Junction to Case (Note 5)		Rejc	1.5	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes:

- 5. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 7. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 8. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

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^{4.} For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

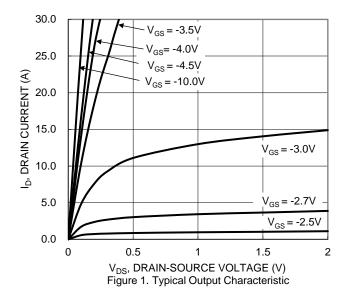
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	-30	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS		_	-1	μΑ	V _{DS} = -24V, V _{GS} = 0V	
Gate-Source Leakage	Igss		_	±10	μΑ	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(TH)	-1.0	_	-3.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance	Dagger		4.5	7	mΩ	$V_{GS} = -10V, I_D = -15A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	1	12	16	11177	$V_{GS} = -4.5V, I_D = -10A$	
Diode Forward Voltage	VsD	1	-0.7	-1.2	V	V _G S = 0V, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 10)	DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}		2,826	_	pF	4514.14	
Output Capacitance	Coss		606	_	pF	$V_{DS} = -15V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss		305	_	pF	T = T.OWHZ	
Gate Resistance	Rg	_	23	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	1	31.2	_	nC		
Total Gate Charge (VGS = -10V)	Qg		64.2	_	nC	V _{DS} = -15V. I _D = -11.5A	
Gate-Source Charge	Qgs		10.6	_	nC	VDS = -15V, ID = -11.5A	
Gate-Drain Charge	Q_{gd}		11.6	_	nC		
Turn-On Delay Time	tD(ON)	_	4.8	_	ns		
Turn-On Rise Time	t _R	_	4.3	_	ns	$V_{DD} = -15V, V_{GS} = -10V$	
Turn-Off Delay Time	tD(OFF)	_	306	_	ns	$R_g = 6\Omega$, $I_D = -11.5A$	
Turn-Off Fall Time	t _F		125	_	ns		
Reverse Recovery Time	t _{RR}		19	_	ns	1a 44 EA dl/dt 4000/:	
Reverse Recovery Charge	QRR	_	9.8	_	nC	Is = -11.5A, dl/dt = 100A/µs	

Notes:

^{9.} Short duration pulse test used to minimize self-heating effect.

^{10.} Guaranteed by design. Not subject to product testing.





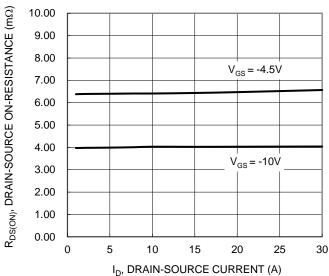


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

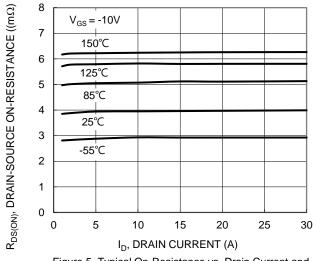
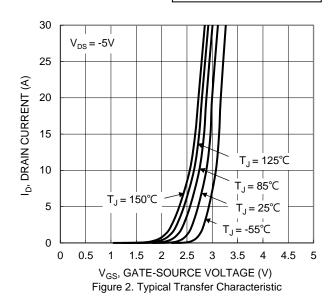
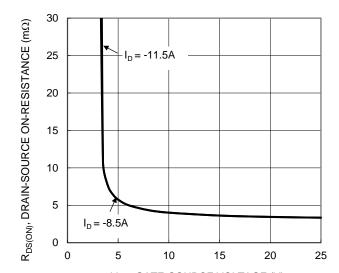


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

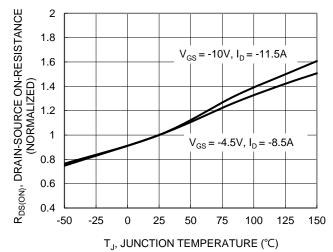


Figure 6. On-Resistance Variation with Temperature



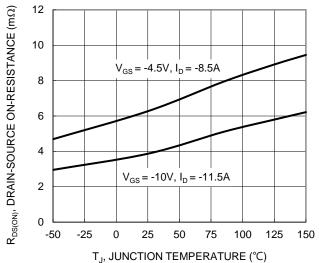
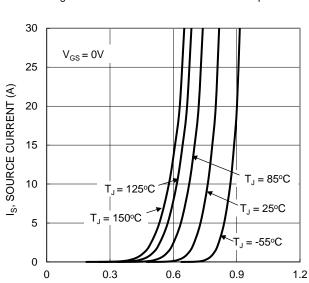


Figure 7. On-Resistance Variation with Temperature



 V_{SD} , SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

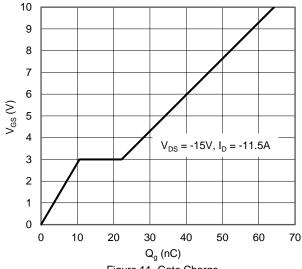


Figure 11. Gate Charge

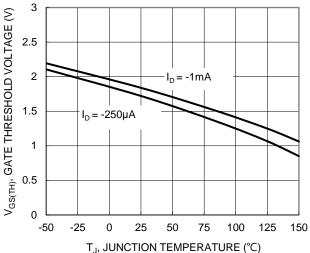
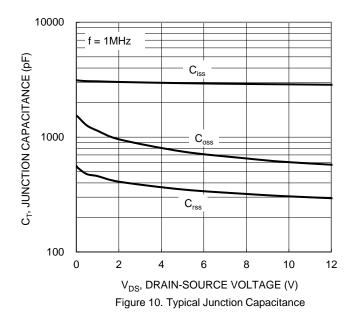


Figure 8. Gate Threshold Variation vs. Junction
Temperature



1000 $R_{DS(ON)}$ Limited 100 ID, DRAIN CURRENT (A) 10 T_{J(Max)} = 150°C $T_C = 25^{\circ}C$ 1 Single Pulse =100ms **DUT** on Infinite Heatsink $V_{GS} = -10V$ 0.1 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



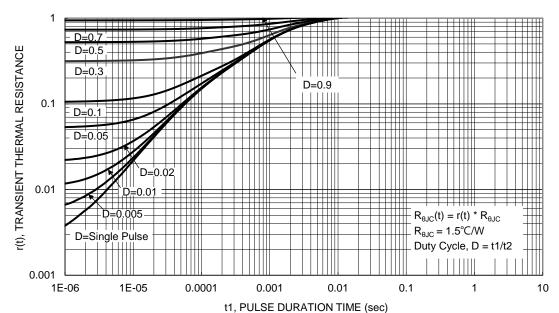


Figure 13. Transient Thermal Resistance

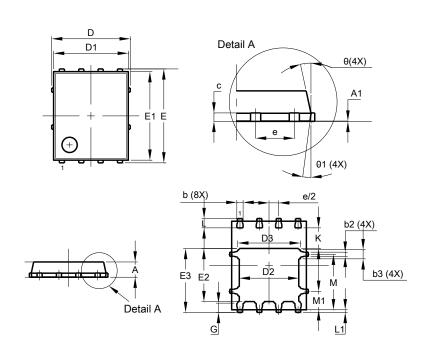


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

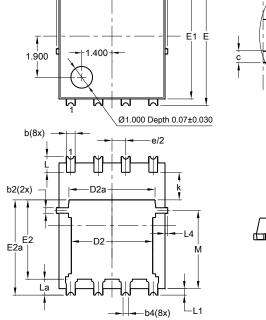
PowerDI5060-8



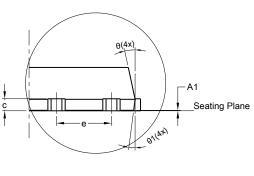
PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D		5.15 BSC		
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
E	(6.15 BSC		
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е		1.27 BSC		
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
M	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

Site 2:

PowerDI5060-8/SWP (Type UX)



-D1



DETAIL A

DETAIL A

PowerDI5060-8/SWP				
(Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4).25REF	=	
С	0.230	0.330	0.277	
D		.15 BS0	2	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
E		.40 BS0		
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е	1	.27BSC)	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
M	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

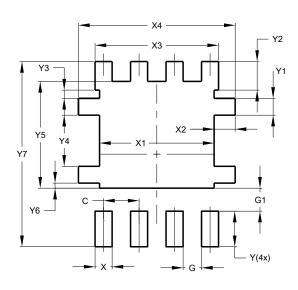


Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

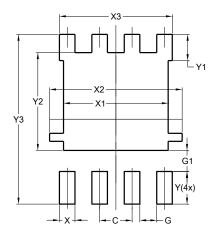
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)



Dimensions	Value
	(in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
Х3	4.420
Υ	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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